

# High-beta Cavity Design

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- **1. SW Operation with SRF RF Cavity**
- 2. Pill Box Cavity
- 3. Figure of merits of SRF Cavity Design
- 4. Criteria for Multi-Cell Structures
- 5. Example of SRF High-beta Cavities

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# **1. Sanding Wave (SW) Operation and Standing Wave in SRF Cavity**

## **SW Scheme in SRF Cavity Operation**



*I<sub>active</sub>* Standing wave (CW) is used in SRF cavity acceleration !

Synchronic acceleration and max of  $(R/Q)_{acc} \leftrightarrow I_{active} = NI_{cell} = NcB/(2f)$  and the injection takes place at an optimum phase  $\varphi_{opt}$  which ensures that particles will arrive at the midplane of the first cell when  $E_{acc}$  reaches its maximum (+q passing to the right) or minimum (-q passing to the right).

$$L_{cell} = \frac{\beta \cdot \lambda}{2}, \qquad \lambda = \frac{c}{f} \qquad \frac{\beta = v/c}{\text{for electron }\beta = 1, \text{ proton }\beta < 1}$$

## **Transit Time Factor Due to SW Operation**





*T* : Transit time factor

 $T = \frac{2}{\pi} = 0.637 \text{ (for Pill Box Cavity)}$  $Eacc \equiv \frac{V}{d} = E_0 T$ 

Acceleration efficiency is automatically reduced by ~ 40% in the SW scheme.

# 2. Pill Box Cavity

## LC Equivalent Circuit of Cavity



## Electro-magnetic field in a waveguide

Maxwell equations in a waveguide

$$\nabla \times \mathbf{E} = i \frac{\omega}{c} \mathbf{B}, \nabla \cdot \mathbf{B} = 0, \nabla \times \mathbf{B} = -i\mu\varepsilon \frac{\omega}{c} \mathbf{E}, \nabla \cdot \mathbf{E} = 0, \rho = 0, \mathbf{j} = 0$$

$$\left(\nabla^{2} + \mu\varepsilon \frac{\omega^{2}}{c^{2}}\right) \left\{ \frac{\mathbf{E}}{\mathbf{B}} \right\} = 0,$$

$$\mathbf{E}(x, y, z, t) = \mathbf{E}(x, y) \exp(\pm ikz - i\omega t), k: \text{ wavevector,}$$

$$\mathbf{B}(x, y, x, t) = \mathbf{B}(x, y) \exp(\pm ikz - i\omega t),$$

$$\left[\nabla_{t}^{2} + (\varepsilon\mu \frac{\omega^{2}}{c^{2}} - k^{2})\right] \left\{ \frac{\mathbf{E}}{\mathbf{B}} \right\} = 0, \nabla_{t}^{2} \equiv \nabla^{2} - \frac{\partial^{2}}{\partial^{2}z}, \quad \mathbf{E} = E_{z}\mathbf{e}_{z} + \mathbf{E}_{t}, \quad \mathbf{B} = B_{z}\mathbf{e}_{z} + \mathbf{B}_{t}$$

$$\left[\nabla_{t}^{2} + (\varepsilon\mu \frac{\omega^{2}}{c^{2}} - k^{2})\right] \left\{ \frac{\mathbf{E}}{\mathbf{B}} \right\} = 0, \nabla_{t}^{2} \equiv \nabla^{2} - \frac{\partial^{2}}{\partial^{2}z}, \quad \mathbf{E} = E_{z}\mathbf{e}_{z} + \mathbf{E}_{t}, \quad \mathbf{B} = B_{z}\mathbf{e}_{z} + \mathbf{B}_{t}$$

$$\left[\nabla_{t}\left(\frac{\partial B_{z}}{\partial z}\right) + i\varepsilon\mu \frac{\omega}{c}\mathbf{e}_{z} \times \nabla_{t}E_{z}\right], \quad \text{Homework I.}$$

$$\left[\mathbf{E}_{t} = \frac{1}{\left(\varepsilon\mu \frac{\omega^{2}}{c^{2}} - k^{2}\right)} \left[\nabla_{t}\left(\frac{\partial E_{z}}{\partial z}\right) - i\frac{\omega}{c}\mathbf{e}_{z} \times \nabla_{t}B_{z}\right], \quad TM \text{ mode: } B_{z} = 0, E_{z} \neq 0$$

$$TE \text{ mode : } B_{z} = 0, E_{z} = 0$$

## **TM- Modes**



Boundary condition  $\mathbf{E}_{\mathbf{z}}|_{\mathbf{S}} = 0$  (  $\therefore$   $\mathbf{n} \times \mathbf{E} = 0$  on the surface of perfect conducto

$$\frac{|B_z|}{|n|} s = 0 (:: \mathbf{n} \cdot \mathbf{B} = 0) \text{ on the surface,}$$

but automatically satisfied by the TM ode condition)

#### Similar for TE modes, which kicks beam.....

## **Eigen-value problem**

 $\psi(x,y) = E_z(x,y)$  for TM- mode or  $B_z(x,y)$  for TE- mode  $\left(\vec{\nabla}_t^2 + \gamma^2\right)\psi = 0, \ \psi|_S = 0$  (for TM-Modes) or  $\frac{\partial}{\partial n}\psi|_S = 0$  (for TE-Modes)

$$\gamma^2 = \varepsilon \mu \cdot \frac{\omega^2}{c^2} - k^2 \ge 0$$

From the boundary condition,

$$\gamma^2 = \gamma_{\lambda}^2, \ \psi = \psi_{\lambda} \quad (\lambda = 1, 2, \cdots) \qquad k_{\lambda}^2 = \varepsilon \mu \frac{\omega^2}{c^2} - \gamma_{\lambda}^2$$
  
If  $\omega < c \frac{\gamma_{\lambda}}{\sqrt{\varepsilon \mu}}$ , then  $k_{\lambda}$  is an imaginal number.

The wave is damped/trapped in the waveguide, if surface resistance large/small.

$$\omega_{\lambda} = c \frac{\gamma_{\lambda}}{\sqrt{\varepsilon \mu}} \cdots$$
 cutoff frequency

When  $\omega \ge \omega_{\lambda}$ , wave number  $k_{\lambda}$  is a real number, then the wave can propagate into the waveguide. 2

$$TM_{m,n,p} - \text{mode}$$

$$E_{z} = E_{o} \cos(kz) J_{m} \left(\frac{\rho_{m,n}}{a}r\right) \exp(-im\theta), \qquad B_{z} = 0$$

$$E_{r} = \frac{iE_{0}p\pi}{\gamma_{m,n,p}} \cos(\frac{p\pi}{d}z) \frac{\partial J_{m}(\rho)}{\partial \rho} \exp(-im\theta), \qquad B_{r} = -\frac{E_{0}m\theta\mu\omega_{m,n,p}}{\gamma_{m,n,p}} \cos(kz) J_{m} \left(\frac{\rho_{m,n}}{a}r\right) \exp(-im\theta)$$

$$E_{\theta} = \frac{E_{0}mp\pi}{\gamma_{m,n,p}^{2}dc} \cos(\frac{p\pi}{d}z) J_{m} \left(\frac{\rho_{m,n}}{a}r\right) \exp(-im\theta), \qquad B_{\theta} = \frac{iE_{0}\varepsilon\mu\omega_{m,n,p}}{\gamma_{m,n,p}c} \cos(kz) \exp(-im\theta) \frac{\partial J_{m}(\rho)}{\partial \rho}$$
resonace frequency
$$\omega_{m,n,p} \Rightarrow f_{m,n,p} = \frac{c}{\sqrt{\varepsilon\mu}} \sqrt{\frac{\rho_{m,n}^{2}}{a^{2}} + \frac{p^{2}\pi^{2}}{d^{2}}}$$

$$TE_{mnp} \text{ Modes}$$

$$E_{z} = 0 \qquad H_{z} = E_{0}J_{m} \left(\frac{\rho'_{mn}}{a}r\right) \cos(m\theta) \sin(\frac{p\pi z}{d})$$

$$E_{r} = \frac{i\omega\varepsilon}{k^{2}} \frac{m}{r} E_{0}J_{m} \left(\frac{\rho'_{mn}}{a}r\right) \sin(m\theta) \sin(\frac{p\pi z}{d}) \qquad H_{r} = \frac{1}{k^{2}} \frac{p\pi}{d} E_{0}J_{m} \left(\frac{\rho'_{mn}}{a}r\right) \sin(m\theta) \cos(\frac{p\pi z}{d})$$

$$E_{\theta} = \frac{i\omega\varepsilon}{k^{2}} \frac{\rho'_{mn}}{a} E_{0}J_{m} \left(\frac{\rho'_{mn}}{a}r\right) \cos(m\theta) \sin(\frac{p\pi z}{d}) \qquad H_{\theta} = -\frac{1}{k^{2}} \frac{p\pi}{d} \frac{m}{r} E_{0}J_{m} \left(\frac{\rho'_{mn}}{a}r\right) \sin(m\theta) \cos(\frac{p\pi z}{d})$$
Resonance frequency
$$\omega^{2}\varepsilon_{0}\mu_{0} = \left(\frac{\rho'_{mn}}{a}\right)^{2} + \left(\frac{p\pi}{d}\right)^{2} \Rightarrow f = \frac{c}{2\pi} \sqrt{\left(\frac{\rho'_{mn}}{a}\right)^{2} + \left(\frac{p\pi}{d}\right)^{2}} 10$$



# **TE**<sub>mnp</sub> **Modes**



# 4. Figure of merits of Cavity Design

## Figure of Merits of The RF Cavity Design

	Items	Notation		
1)	Surface resistance	$R_{S}[\Omega]$		
2)	RF dissipation	P <sub>loss</sub> [W]		
3)	Acceleration gradient	V[V]		
3)	Unloaded Q	Q <sub>O</sub>		
4)	Geometrical factor	Γ[Ω]		
5)	Shunt Impedance	Rsh[Ω]		
6)	R over Q	(R/Q) [Ω]		
7)	Acceleration gradient	Eacc[V/m]		
8)	Ratio of the surface peak electric field vs Eacc	Ep/Eacc		
		[Oe/(MV/m)		
9)	Ratio of the surface magnetic field vs Eacc	Hp/Eacc		
10)	HOM loss factor			
11)	Field flatness factor	a <sub>ff</sub>		
12)	Cell to cell coupling	k <sub>CC</sub>		

## **Surface Resistance**

#### Maxwell Equations.

$$\nabla \cdot \vec{B} = 0, \ \nabla \times \vec{E} + \mu \frac{\partial \vec{H}}{\partial t} = 0$$
$$\nabla \cdot \vec{D} = 0, \ \nabla \times \vec{H} - \varepsilon \frac{\partial \vec{E}}{\partial t} - \sigma \vec{E} = 0$$
$$\vec{J} = \sigma \vec{E} \quad \text{(Ohm's Law)}$$

 $\vec{\mathrm{E}}(\vec{\mathrm{x}},t) = \vec{\mathrm{E}}_{\ell}(\vec{\mathrm{x}},t) + \vec{\mathrm{E}}_{\mathrm{t}}(\vec{\mathrm{x}},t),$  $\vec{\mathrm{H}}(\vec{\mathrm{x}},t) = \vec{\mathrm{H}}_{\ell}(\vec{\mathrm{x}},t) + \vec{\mathrm{H}}_{\mathrm{t}}(\vec{\mathrm{x}},t)$ 

For the transvers,

Plane wave :  $\vec{E}_t(\vec{x},t) = \vec{E}_t(0) \cdot \exp(i\vec{k} \cdot \vec{x} - \omega t)$ 

$$\vec{H}_{t}(\mathbf{x},t) = \frac{1}{\mu\omega} [\vec{k} \times \vec{E}_{t}(\vec{x},t)],$$
$$[k^{2} - (\varepsilon\mu\omega^{2} + i\mu\omega\sigma)] \begin{cases} \vec{E}_{t}(\vec{x},t) \\ \vec{H}_{t}(\vec{x},t) \end{cases} = 0$$

Rs: Surface resistance Surface Impedance  

$$Z \equiv R_{s}^{\downarrow} + iX_{s} \equiv \frac{E_{t}}{H_{t}} \Big|_{Surface} = \frac{\mu\omega}{k}$$
Homework II  
Lead the formula of Rs  
for good electric conductor  

$$\mathbf{R}_{s} = \sqrt{\frac{\mu\omega}{2\sigma}} = \frac{1}{\sigma} \sqrt{\frac{\mu\sigma\omega}{2}} = \frac{1}{\sigma\delta}$$

$$P_{loss} = \frac{1}{2} \mathbf{R}_{s} \cdot \int_{S} \mathbf{H}_{s}^{2} dS$$

### **Charismatic RF Parameter of Cavity**



*U* ≡ stored energy, Ploss:Surface RF Heating

$$U = \frac{1}{2} \cdot \varepsilon \int_{V} E^{2} dV = \frac{1}{2} \cdot \mu \int_{V} H^{2} dV$$
$$P_{loss} = \frac{1}{2} \cdot R_{S} \int_{S} H_{S}^{2} dS$$
$$Q_{O} \equiv \frac{\omega U}{P_{loss}}$$

For acceleration mode (TM010), the higher Qo is better.

Acceleration Voltage $V[V] = \int_0^{L_{eff}} E dz$  on the beam axis.Shunt Impedance $R_{sh}[\Omega] \equiv \frac{V^2}{P_{loss}}$ 

This means the efficiency of the acceleration.

**Charismatic RF Parameter of Cavity, continued.** 

(**R**/**Q**) 
$$(R/Q) \equiv (R_{sh}/Q_O) = \frac{V^2}{\omega U}$$

This means how much energy is concentrated on beam axis. This does not depend on material but only cavity shape. This means the goodness of the cavity shape.

**Geometrical factor** 
$$\Gamma[\Omega] \equiv Q_O \cdot R_S = \frac{\omega \int_V H^2 dV}{\frac{1}{2} \int_S H_S^2 dS}$$

When you know the  $\Gamma$  using a computer code, you can calculate the surface resistance  $R_S$  from the measured  $Q_O$  value.

 $\Gamma$  is about 270 $\Omega$  for  $\beta$ =1 cavities with elliptical or spherical shape.

### **Charismatic RF Parameter of Cavity**



Smaller value is preferred against electron emission phenomenon.

Ratio shows the limit in  $E_{acc}$  due to the break-down of superconductivity (Nb ~2000 Oe ).

### Longitudinal and Transverse Loss Factors

When ultra relativistic point charge q passes empty cavity,



HOM modes are excited in the cavity.

If those are damped fast enough, the following beam feel them and can be kicked.

Thus the beam can be degradated.

## $(R/Q)_n$ of n-th HOM

HOM nth  $(R/Q)_n$ , a "measure" of the energy exchange between point charge and mode n .\_



#### Longitudinal and Transverse Loss Factors

The amount of energy lost by charge q to the cavity is:  $\Delta U_q = k_{\parallel} \cdot q^2 \quad \text{for monopole modes (max. on axis)}$   $\Delta U_q = k_{\perp} \cdot q^2 \quad \text{for non monopole modes (off axis)}$ 

where  $\mathbf{k}_{\parallel}$  and  $\mathbf{k}_{\perp}(\mathbf{r})$  are loss factors for the monopole and transverse modes respectively.

The induced **E-H field (wake)** is a superposition of <u>cavity eigenmodes</u> (monopoles and others) having the  $E_n(r,\varphi,z)$  field <u>along the trajectory</u>.

For individual mode n and point-like charge:

$$k_{\parallel,n}^{\mathbf{p}} = \frac{\omega_n \cdot (R/Q)_n}{4}$$

Similar for other loss factors......

These harmful HOM power should be take out from the cavity. <sub>21</sub> Dr. Noguchi will make a lecture about the HOM coupler design.

### **Field Flatness Factor** a<sub>ff</sub>

J.Sekutwitz's Slide

**B**<sub>2</sub>

Field flatness factor for elliptical cavities with arbitrary ß=v/c

$$\frac{\Delta A}{A} = a_{ff} \cdot \frac{\Delta f}{f} \qquad \qquad \mathbf{a}_{ff} = \frac{N^2}{k_{cc} \cdot \beta}$$

This is an empirical correction, based on intuition.



Cells which geometric ß <1 are more sensitive to shape errors

## Cell to cell coupling $\mathbf{k}_{\text{CC}}$

The last parameter, relevant for multi-cell accelerating structures, is the coupling  $\mathbf{k}_{cc}$  between cells for the accelerating mode pass-band (Fundamental Mode pass-band).

ω



 $\omega_{\pi}$ 

no E<sub>r</sub> (in general transverse E field) component at the symmetry plane no  $H_{\varphi}$  (in general transverse H field) component at the symmetry plane

The normalized difference between these frequencies is a measure of the Poynting vector (energy flow via the coupling region)

$$k_{cc} = \frac{\omega_{\pi} - \omega_{0}}{\frac{\omega_{\pi} + \omega_{0}}{2}}$$

## Spherical/Elliptical Shape in SRF cavity design

Design of SRF cavity is usually done with spherical or Elliptical shapes.



R. Parodi (1979) presented first **spherical** C-band cavity with much less multipacting barrier than other cavities at that time.

*P. Kneisel (early 80's)* proposed for the DESY experiment the **elliptical shape** of 1 GHz cavity preserving good performance of the spherical one and stiffer mechanically.

The RF cavity design tool will be given by Dr. U. van Rienen In this tutorial.

## **Optimization of Cell Shape**

We begin with inner cells design because these cells "dominate" parameters of a multi-cell superconducting accelerating structure. **RF parameters summary:**J.Sekutwitz's Slide

$$FM : (R/Q), G, E_{peak}/E_{acc}, B_{peak}/E_{acc}, k_{cc}$$
$$HOM : k_{\perp}, k_{\parallel}.$$

There are 7 parameters we want to optimize for a inner cell Geometry :



There is some kind of conflict <u>7 parameters</u> and only <u>5 variables</u> to "tune"

#### **Effect of Cavity Aperture on RF Parameters**



A. Mosnier, E. Haebel, SRF Workshop 1991

### Aperture Effects on $\kappa_{//}$ and $\kappa_{\perp}$ )



$$(R/Q) = 152 \Omega$$
$$B_{peak} / E_{acc} = 3.5 mT/(MV/m)$$
$$E_{peak} / E_{acc} = 1.9$$

 $(R/Q) = 86 \Omega$  $B_{peak} / E_{acc} = 4.6 mT/(MV/m)$  $E_{peak} / E_{acc} = 3.2$ 

### Aperture Effect on Cell to Cell Coupling ( $\kappa_{CC}$ )

#### J.Sekutwitz's Slide



 $(R/Q) = 152 \Omega$  $B_{peak} / E_{acc} = 3.5 mT/(MV/m)$  $E_{peak} / E_{acc} = 1.9$ 

 $(R/Q) = 86 \Omega$  $B_{peak} / E_{acc} = 4.6 mT/(MV/m)$  $E_{peak} / E_{acc} = 3.2$ 

#### **General Trends of Cavity Optimization on RF Geometrical Parameters**



### **Choice of the RF Frequency**

What about accelerating mode frequency of a superconducting cavity?



 $r/q=(R/Q)/l \sim f$ 

## **Frequency Choice of the SRF Cavity**



#### **TESLA Cavity Inner Cell Shape**

The inner cell geometry was optimize with respect to: low  $E_{peak}/E_{acc}$  and coupling  $k_{cc}$ .

At that time (1992) the field emission phenomenon and field flatness were of concern, no one was thinking about reaching the magnetic limit.

$f_{\pi}$	[MHz]	1300.0
r <sub>iris</sub>	[mm]	35
k <sub>cc</sub>	[%]	1.9
$E_{peak}/E_{acc}$	-	1.98
B <sub>peak</sub> /E <sub>acc</sub>	[mT/(MV/m)]	4.15
R/Q	[Ω]	113.8
G	[Ω]	271
<i>R/Q*G</i>	[Ω*Ω]	30840



Inner cell; Contour of E field

## **High Gradient Shapes**

### **Cavity shape designs with low Hp/Eacc**

**TTF: TESLA shape Reentrant (RE): Cornell Univ.** TTF LL RE Low Loss(LL): JLAB/DESY Ichiro-Single (IS): KEK 1992 2002/2004 2002 TESLA LL RE IS **Diameter** [mm] 70 60 66 61 **Ep/Eacc** 2.0 2.36 2.21 2.02 Hp/Eacc [Oe/MV/m] 42.6 36.1 37.6 35.6 **R/Q** [W] 113.8 133.7 126.8 138 G[W]271 284 277 285 41.1 48.5 46.5 49.2 Eacc max

#### <u>from J.Sekutowicz lecture No</u>t

### Eacc vs. Year

#### 2<sup>nd</sup> Breakthrough!



## 4. Criteria for Multi-cell Structures

Single-cell is attractive from the RF-point of view:

- Easier to manage HOM damping
- No field flatness problem.
- Input coupler transfers less power
- Easy for cleaning and preparation
- But it is expensive to base even a small linear accelerator on the single cell. We do it only for very high beam current machines.

A multi-cell structure is less expensive and offers higher real-estate gradient but:

- Field flatness (stored energy) in cells becomes sensitive to frequency errors of individual cells
- Other problems arise: HOM trapping...

How to decide the number of cells ?

# =0000000000000000000

## **Parameters considered with N**

 $\rightarrow \frac{\Delta A_i}{A_i} = a_{ff} \frac{\Delta f_i}{f_i} = \frac{N^2}{k_{cc}} \cdot \frac{\Delta f_i}{f_i}$  Beam pipe has no acceleration beam. BP reduce the efficiency.

Multi-cell is more efficient.

RF

**Field flatness factor :** 

HOM

$$a_{ff} = \frac{N^2}{k_{cc}}$$

**HOM trapped mode :** 

More serious within creasing N

**Input handling power :**  $P_{INPUT} \propto N$ 36 **Handling :** Easy to bend, Difficult to preparation .....

## **Effect of N on Field Flatness Sensitivity Factor**

#### J.Sekutwitz's Slide

#### Field flatness vs. N

	Original Cornell N = 5	High Gradient N=7	Low Loss N=7	TESLA N=9	SNS B=0.61 N=6	SNS B=0.81 N=6	RIA B=0.47 N=6	RHIC N=5
year	1982	2001	2002	1992	2000	2000	2003	2003
a <sub>ff</sub>	1489	2592	3288	4091	3883	2924	5040	850

Many years of experience with: heat treatment, chemical treatment, handling and assembly allows one to preserve tuning of cavities, even for those with bigger N and weaker  $k_{cc}$ 

For the TESLA cavities: field flatness is better than 95 %

## HOM trapping vs. N

J.Sekutwitz's Slide

No fields at HOM couplers positions, which are always placed at end beam tubes



e-m fields at HOM couplers positions

Cure for the trapped mode: Make the bore radius larger. Break mirror symmetry.

## **HOM Issue with Multi-Cell Structure**

#### HOM couplers limit RF-performance of sc cavities when they are placed on cells

no E-H fields at HOM couplers positions, which are always placed at end beam tubes



The HOM trapping mechanism is similar to the FM field profile unflatness mechanism:

- weak coupling HOM cell-to-cell, к<sub>сс,ном</sub>
- ✤ difference in HOM frequency of end-cell and inner-cell

f = 2385 MHz



That is why they hardly resonate together



f = 2415 MHz

J.Sekutwitz's Slide

## Adjustment of End-Cells

#### J.Sekutwitz's Slide

The geometry of end-cells differs from the geometry of inner cells due to the attached beam tubes



Their function is multi-folded and their geometry must fulfill three requirements:

- ✤ field flatness and frequency of the accelerating mode
- field strength of the accelerating mode at FPC location enabling operation with matched Qext
- fields strength of dangerous HOMs ensuring their required damping by means of HOM couplers or/and beam line absorbers.

All three make design of the end-cells more difficult than inner cells.

## **Capable Input Power on N**

#### • Power capability of fundamental power couplers vs. N

When  $I_{beam}$  and  $E_{acc}$  are specified and a superconducting multi-cell structure does not operate in the energy recovery mode:

Coupler handling power limits the small N in the intensity frontier machine like KEK B(N=1). KEKB: Acceleration beam current > 1 A.

#### **TESLA/ILC Baseline Cavity**

The cavity was designed in 1992 (A. Mosnier, D. Proch and J.S.).



TTF 9-cells; Contour of E field

$f_{\pi}$	[MHz]	1300.00
f <sub>π-1</sub>	[MHz]	1299.24
R/Q	$[\Omega]$	1012
G	$[\Omega]$	271
Active length	[mm]	1038

## **Overview of Cavities**

J.Sekutwitz's Slide

Examples of Inner cells		new	new				new	new	
		CEBAF Original Cornell ß=1	CEBAF -12 High Gradient <b>ß</b> =1	CEBAF -12 Low Loss <b>ß</b> =1	TESLA ß=1	SNS B=0.61	SNS B=0.81	RIA ß=0.47	RHIC Cooler ß=1
$f_o$	[MHz]	1448.3	1468.9	1475.1	1278.0	792.8	792.8	793.0	683.0
$f_{\pi}$	[MHz]	1497.0	1497.0	1497.0	1300.0	805.0	805.0	805.0	703.7
k <sub>cc</sub>	[%]	3.29	1.89	1.49	1.9	1.52	1.52	1.52	2.94
$E_{peak}/E_{acc}$	-	2.56	1.96	2.17	1.98	2.66	2.14	3.28	1.98
$B_{peak}/E_{acc}$	[mT/(MV/m)]	4.56	4.15	3.74	4.15	5.44	4.58	6.51	5.78
R/Q	[Ω]	96.5	112	128.8	113.8	49.2	83.8	28.5	80.2
G	[Ω]	273.8	266	280	271	176	226	136	225
R/Q*G	/Ω*Ω/	26421	29792	36064	30840	8659	18939	3876	18045
$k_{\perp}$ ( $\sigma_z=1mm$ )	[V/pC/cm <sup>2</sup> ]	0.22	0.32	0.53	0.23	0.13	0.11	0.15	0.02
$k_{\parallel}$ ( $\sigma_z=1mm$ )	[V/pC]	1.36	1.53	1.71	1.46	1.25	1.27	1.19	0.85

**β vs RF parameters** 

 $\beta$  smaller

Ep/Eacc larger

Hp/Eacc larger (R/Q) smaller

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# 5. Example of SRF High-beta Cavities

#### J.Sekutwitz's Slide

Cavities operating with highest  $I_{beam}$  or  $E_{acc}$ 

<i>Type /No. of cavities</i>			P <sub>beam</sub> /cavity [kW]	P <sub>HOM</sub> /cavity [kW]
KEK-B 0.5 GHz	Single-cell 8 with max I <sub>beam</sub>	I <sub>beam</sub> = 1.34 A 1389 bunches cw	350	16
HERA 0.5 GHz	Multi-cell with max I <sub>beam</sub>	I <sub>beam</sub> ≤ 40 mA 180 bunches cw	60	0.13
TTF-I , 1.3 GHz	$\frac{Multi-cell}{with max E_{acc}}$	E <sub>acc</sub> = 35 MV/m 1.3ms/pulse 1Hz PRF	~100 Almost no beam loading	0

#### J.Sekutwitz's Slide

#### Cavities which will operate with high $I_{beam}$ in the near future

Type /No. cavities				P <sub>beant</sub> /cavity [kW]	P <sub>HOM</sub> /cavity [kW]
SNS ß= 0.61, 0.805 GHz	c 33	Multi-cell with max	I <sub>beam</sub> =38 (59) mA 1.3ms/pulse DF = 6 %	240 (366)	0.06 peak
SNS ß= 0.805 GHz	c 48	I <sub>beam</sub>		482	0.06 peak
TTF-II ep , 1.3 GHz	x 8	Multi-cell with max E <sub>acc</sub>	E <sub>acc</sub> = 35 MV/m 1.3ms/pulse 10Hz PRF	146	< 0.02>